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				Application Number	
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				Examiner Name	
Attorney Docket Number		88103.0001			
Sheet	1	of	1		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		Chin-hsing Yu, et al., Ultrathin (2.7nm) Oxy-nitride for Suppressing Boron Penetration Characterized by Direct Hole Tunneling Current in p+/pMOS, Technology Development Center, Worldwide Semiconductor Manufacturing Corp., Hsinchu, Taiwan 30077, Republic of China	
		S.C. Song, et al., Ultra Thin high quality stack nitride/oxide gate dielectrics prepared by <i>in-situ</i> rapid thermal N ₂ O oxidation of NH ₃ -nitrided Si, Microelectronics Research Center, Department of Electrical and Computer Engineering The University of Texas, Austin, TX	
		Quazi D. M., Khosru, et al., Low Thermal-Budget Ultrathin NH ₃ -Annealed Atomic-Layer-Deposited Si-Nitride/SiO ₂ Stack Gate Dielectrics With Excellent Reliability, IEEE Electron Device Letters, Vol. 23, No. 4, April 2002	
		Quazi D.M., Khosru, et al., Ultrathin NH ₃ Annealed Atomic Layer Deposited Si-nitride/SiO ₂ Stack Gate Dielectrics with High Reliability, Research Centr for Nanodevices and Systems, Hiroshima University, 1-4-2 Kagamiyama, Higashi-Hiroshima, Japan	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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